

Golden List of Reviewers for 2022

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Peng-Ying	Chang	Peking University	China
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Bing	Chen	Zhejiang University	China
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Dunjun	Chen	Nanjing University	China

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Jun	Chen	Sun Yat-sen University	China
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Lining	Zhang	Shenzhen University	China
Long	Zhang	Southeast University	China
Luqi	Zhang	China Academy of Engineering Physics	China
Meng	Zhang	Shenzhen University	China
Min	Zhang	Peking University	China
Peng	Zhang	Michigan State University	United States
Putao	Zhang	Henan University	China
Rong	Zhang	Xiamen University	China
Rui	Zhang	Zhejiang University	China
Shengdong	Zhang	Peking University	China
Shengli	Zhang	Nanjing University of Science and Technology	China
Shiyong	Zhang	China Academy of Engineering Physics	China
Shuye	Zhang	Harbin Institute of Technology	China
Wei	Zhang	Liverpool John Moores University	United Kingdom
Wentong	Zhang	University of Electronic Science and Technology of China	China

Yiqiang	Zhang	Zhengzhou University	China
Yong	Zhang	University of Electronic Science and Technology of China	China
Yong	Zhang	University of North Carolina at Charlotte	United States
Yue	Zhang	Beihang University	China
Yuhao	Zhang	Virginia Tech	United States
Zhaofu	Zhang	Cambridge University	United Kingdom
Zhaohao	Zhang	Institute of Microelectronics of the Chinese Academy of Sciences	China
Zhipeng	Zhang	Shenyang Institute of Automation Chinese Academy of Sciences	China
Zhiyong	Zhang	Institution of Physical Electronics	China
Zi-Hui	Zhang	Hebei University of Technology	China
Chun	Zhao	University of Cambridge	United Kingdom
Dewei	Zhao	Sichuan University	China
Ding	Zhao	Institute of Electronics, Chinese Academy of Sciences	China
Hongping	Zhao	Ohio Sate University	United States
Jiahao	Zhao	Tsinghua University	China
Junping	Zhao	Xi'an Jiaotong University	China
Qinghua	Zhao	Northwestern Polytechnical University	China
Qing-Tai	Zhao	Forschungszentrum Jülich GmbH	Germany
Qixiang	Zhao	Guilin University of Electronic Technology	China
Shenglei	Zhao	Xidian University	China
Weisheng	Zhao	Beihang University	China
Wen-Sheng	Zhao	Hangzhou Dianzi University	China
Yudi	Zhao	Peking University	China
Huai	Zheng	Wuhan University	China
Yongju	Zheng	SemiQ, Inc.	United States
Yuan	Zheng	University of California Davis	United States
Yuan	Zheng	University of Electronic Science and Technology of China	China
Zheyang	Zheng	Hong Kong University of Science and Technology	Hong Kong
Zijian	Zheng	Hong Kong Polytechnic University	Hong Kong
Changjian	Zhou	South China University of Technology	China
Guanghui	Zhou	Hunan Normal University	China
Haidi	Zhou	Ferroelectric Memory Company GmbH	Germany
Hong	Zhou	Xidian University	China
Jiuren	Zhou	Xidian University	China
Liang	Zhou	Shanghai JiaoTong University	China
Min-Bo	Zhou	South China University of Technology	China
Peng	Zhou	Fudan University	China
Qi	Zhou	University of Electronic Science and Technology of China	China
Qiaogen	Zhou	-	China
Wei	Zhou	Hong Kong University of Science and Technology	Hong Kong
Xin	Zhou	University of Electronic Science and Technology of China	China
Xintian	Zhou	Beijing University of Technology	China
Yichun	Zhou	Xiangtan University	China
Yuanzhong	Zhou	Analog Devices Inc.	United States
Yugang	Zhou	Nanjing University	China
Zheng	Zhou	Peking University	China

Huilong	Zhu	Institute of Microelectronics of the Chinese Academy of Sciences	China
Jiejie	Zhu	Xidian University	China
Li Qiang	Zhu	Ningbo University	China
Peifen	Zhu	University of Missouri	United States
Qing	Zhu	Xidian University	China
Xiaona	Zhu	Fudan University	China
Ying Bin	Zhu	South China University of Technology	China
Yuan	Zhu	Shanghai Jiao Tong University	China
Zonglong	Zhu	City University of Hong Kong	Hong Kong
Fei	Zhuge	Ningbo Institute of Material of Technology & Engineering, CAS	China
Yunlong	Zi	Chinese University of Hong Kong	Hong Kong
Martin	Ziegler	Technische Universitat Ilmenau	Germany
Thomas	Zimmer	Université de Bordeaux	France
Sandra	Zivanovic	Louisiana Tech University	United States
Cezar	Zota	IBM Zurich Research Laboratory	Switzerland
Xiao	Zou	Jiangnan University	China
Ahmad	Zubair	Intel Corporation	United States